



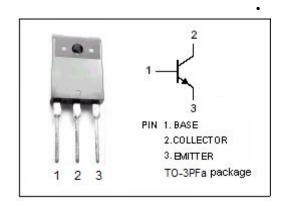
# **isc Silicon NPN Power Transistor**

### **DESCRIPTION**

- · Collector-Base Breakdown Voltage-
  - : V<sub>(BR)CBO</sub>= 800V(Min.)
- Low Collector Saturation Voltage
- · High Speed Switching
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

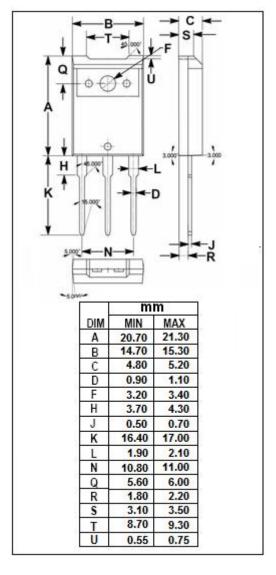
#### **APPLICATIONS**

· Designed for high speed switching applications.



# ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>СВО</sub>	Collector-Base Voltage	800	V
V <sub>CES</sub>	Collector-Emitter Voltage	800	V
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V
V <sub>EBO</sub>	Emitter-Base Voltage	8	V
Ic	Collector Current-Continuous	5	А
Ісм	Collector Current-Peak	10	А
Ι <sub>Β</sub>	Base Current-Continuous	3	А
Pc	Collector Power Dissipation @T <sub>a</sub> =25℃	3 W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	70	VV
T <sub>j</sub>	Junction Temperature	150	${\mathbb C}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}\mathbb{C}$





# isc Silicon NPN Power Transistor

2SC3798

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

10-20 C unless otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	500			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.0	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.5	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			100	μА			
ІЕВО	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μА			
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	15						
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	8						
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V; f= 1MHz		8		MHz			
Switching Times									
t <sub>on</sub>	Turn-on Time				1.0	μS			
ts	Storage Time	I <sub>C</sub> = 3A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.6A; V <sub>CC</sub> = 200V			3.0	μS			
tf	Fall Time				1.0	μS			

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